

Timothy D Sands

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218
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10,802
ext. citations

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L-index

#	Paper	IF	Citations
218	Titanium nitride as a plasmonic material for visible and near-infrared wavelengths. <i>Optical Materials Express</i> , 2012 , 2, 478	2.6	468
217	Fatigue and retention in ferroelectric Y-Ba-Cu-O/Pb-Zr-Ti-O/Y-Ba-Cu-O heterostructures. <i>Applied Physics Letters</i> , 1992 , 61, 1537-1539	3.4	335
216	Damage-free separation of GaN thin films from sapphire substrates. <i>Applied Physics Letters</i> , 1998 , 72, 599-601	3.4	322
215	Ferroelectric La-Sr-Co-O/Pb-Zr-Ti-O/La-Sr-Co-O heterostructures on silicon via template growth. <i>Applied Physics Letters</i> , 1993 , 63, 3592-3594	3.4	314
214	Nanoscale design to enable the revolution in renewable energy. <i>Energy and Environmental Science</i> , 2009 , 2, 559	35.4	311
213	Equilibrium limits of coherency in strained nanowire heterostructures. <i>Journal of Applied Physics</i> , 2005 , 97, 114325	2.5	301
212	Fabrication of thin-film InGaN light-emitting diode membranes by laser lift-off. <i>Applied Physics Letters</i> , 1999 , 75, 1360-1362	3.4	284
211	Electrodeposition of ordered Bi ₂ Te ₃ nanowire arrays. <i>Journal of the American Chemical Society</i> , 2001 , 123, 7160-1	16.4	271
210	Fabrication of High-Density, High Aspect Ratio, Large-Area Bismuth Telluride Nanowire Arrays by Electrodeposition into Porous Anodic Alumina Templates. <i>Advanced Materials</i> , 2002 , 14, 665-667	24	261
209	Insights into the Electrodeposition of Bi ₂ Te ₃ . <i>Journal of the Electrochemical Society</i> , 2002 , 149, C546	3.9	207
208	Epitaxial growth of ferromagnetic ultrathin MnGa films with perpendicular magnetization on GaAs. <i>Applied Physics Letters</i> , 1993 , 62, 1565-1567	3.4	185
207	Epitaxial superlattices with titanium nitride as a plasmonic component for optical hyperbolic metamaterials. <i>Proceedings of the National Academy of Sciences of the United States of America</i> , 2014 , 111, 7546-51	11.5	164
206	Structure of Bismuth Telluride Nanowire Arrays Fabricated by Electrodeposition into Porous Anodic Alumina Templates. <i>Chemistry of Materials</i> , 2003 , 15, 335-339	9.6	160
205	In _x Ga _{1-x} N light emitting diodes on Si substrates fabricated by Pd ₁₀ metal bonding and laser lift-off. <i>Applied Physics Letters</i> , 2000 , 77, 2822-2824	3.4	159
204	Direct Electrodeposition of Highly Dense 50 nm Bi ₂ Te ₃ -ySey Nanowire Arrays. <i>Nano Letters</i> , 2003 , 3, 973-977	11.5	140
203	Oriented ferroelectric La-Sr-Co-O/Pb-La-Zr-Ti-O/La-Sr-Co-O heterostructures on [001] Pt/SiO ₂ Si substrates using a bismuth titanate template layer. <i>Applied Physics Letters</i> , 1994 , 64, 2511-2513	3.4	134
202	High-Density 40 nm Diameter Sb-Rich Bi ₂ Sb _x Te ₃ Nanowire Arrays. <i>Advanced Materials</i> , 2003 , 15, 1003-1006	10.6	130

201	The electrodeposition of high-density, ordered arrays of Bi _{1-x} Sb _x nanowires. <i>Journal of the American Chemical Society</i> , 2003 , 125, 2388-9	16.4	118
200	Effects of crystalline quality and electrode material on fatigue in Pb(Zr,Ti)O ₃ thin film capacitors. <i>Applied Physics Letters</i> , 1993 , 63, 27-29	3.4	115
199	Epitaxial ferromagnetic [MnAl] films on GaAs. <i>Applied Physics Letters</i> , 1990 , 57, 2609-2611	3.4	110
198	A comparative study of phase stability and film morphology in thin-film M/GaAs systems (M=Co, Rh, Ir, Ni, Pd, and Pt). <i>Journal of Applied Physics</i> , 1987 , 62, 2070-2079	2.5	104
197	Electronic structure, phonons, and thermal properties of ScN, ZrN, and HfN: A first-principles study. <i>Journal of Applied Physics</i> , 2010 , 107, 033715	2.5	102
196	Thermal conductivity of (Zr,W)N/ScN metal/semiconductor multilayers and superlattices. <i>Journal of Applied Physics</i> , 2009 , 105, 024909	2.5	101
195	Ferroelectric PbZr _{0.2} Ti _{0.8} O ₃ thin films on epitaxial Y-Ba-Cu-O. <i>Applied Physics Letters</i> , 1991 , 59, 3542-3544	3.4	101
194	Dislocation filtering in GaN nanostructures. <i>Nano Letters</i> , 2010 , 10, 1568-73	11.5	100
193	Heterogeneous integration of CdS filters with GaN LEDs for fluorescence detection microsystems. <i>Sensors and Actuators A: Physical</i> , 2004 , 111, 1-7	3.9	97
192	Solid-phase regrowth of compound semiconductors by reaction-driven decomposition of intermediate phases. <i>Journal of Materials Research</i> , 1988 , 3, 914-921	2.5	96
191	Structure and composition of Ni _x GaAs. <i>Applied Physics Letters</i> , 1986 , 48, 402-404	3.4	94
190	Faceted and vertically aligned GaN nanorod arrays fabricated without catalysts or lithography. <i>Nano Letters</i> , 2005 , 5, 1847-51	11.5	93
189	Molecular beam epitaxial growth of ultrathin buried metal layers: (Al,Ga)As/NiAl/(Al,Ga)As heterostructures. <i>Applied Physics Letters</i> , 1988 , 53, 1717-1719	3.4	87
188	Stability and epitaxy of NiAl and related intermetallic films on III-V compound semiconductors. <i>Applied Physics Letters</i> , 1988 , 52, 197-199	3.4	86
187	Effect of crystallographic orientation on ferroelectric properties of PbZr _{0.2} Ti _{0.8} O ₃ thin films. <i>Applied Physics Letters</i> , 1993 , 63, 731-733	3.4	83
186	Reduction of the energy gap pressure coefficient of GaN due to the constraining presence of the sapphire substrate. <i>Journal of Applied Physics</i> , 1999 , 85, 2385-2389	2.5	78
185	ErAs epitaxial layers buried in GaAs: Magnetotransport and spin-disorder scattering. <i>Physical Review Letters</i> , 1989 , 62, 2309-2312	7.4	77
184	GaN nanorod Schottky and p-n junction diodes. <i>Nano Letters</i> , 2006 , 6, 2893-8	11.5	74

183	Initial stages of the Pd-GaAs reaction: Formation and decomposition of ternary phases. <i>Thin Solid Films</i> , 1986 , 136, 105-122	2.2	73
182	Van der Waals bonding of GaAs on Pd leads to a permanent, solid-phase-topotaxial, metallurgical bond. <i>Applied Physics Letters</i> , 1991 , 59, 3159-3161	3.4	72
181	Thermoelectric properties of epitaxial ScN films deposited by reactive magnetron sputtering onto MgO(001) substrates. <i>Journal of Applied Physics</i> , 2013 , 113, 153704	2.5	71
180	Laser-driven formation of a high-pressure phase in amorphous silica. <i>Nature Materials</i> , 2003 , 2, 796-800	27	69
179	Thermal properties of electrodeposited bismuth telluride nanowires embedded in amorphous alumina. <i>Applied Physics Letters</i> , 2004 , 85, 6001-6003	3.4	68
178	Anisotropic Effects on the Thermoelectric Properties of Highly Oriented Electrodeposited Bi ₂ Te ₃ Films. <i>Scientific Reports</i> , 2016 , 6, 19129	4.9	65
177	Electrodeposition of Bi _{1-x} Sb _x Films and 200-nm Wire Arrays from a Nonaqueous Solvent. <i>Chemistry of Materials</i> , 2003 , 15, 1676-1681	9.6	64
176	Epitaxial growth of GaAs/NiAl/GaAs heterostructures. <i>Applied Physics Letters</i> , 1988 , 52, 1216-1218	3.4	63
175	Negative differential resistance in AlAs/NiAl/AlAs heterostructures: Evidence for size quantization in metals. <i>Applied Physics Letters</i> , 1988 , 53, 2528-2530	3.4	62
174	An investigation of a nonspiking Ohmic contact to n-GaAs using the Si/Pd system. <i>Journal of Materials Research</i> , 1988 , 3, 922-930	2.5	62
173	Thermoelectric Transport in a ZrN/ScN Superlattice. <i>Journal of Electronic Materials</i> , 2009 , 38, 960-963	1.9	58
172	The atomic structure of growth interfaces in YBaCuO thin films. <i>Journal of Materials Research</i> , 1991 , 6, 2264-2271	2.5	58
171	Ferroelectric bismuth titanate/superconductor (Y-Ba-Cu-O) thin-film heterostructures on silicon. <i>Applied Physics Letters</i> , 1991 , 59, 1782-1784	3.4	56
170	Surface outgrowth problem in c-axis oriented Y-Ba-Cu-O superconducting thin films. <i>Applied Physics Letters</i> , 1991 , 58, 1557-1559	3.4	56
169	Cross-plane thermal conductivity of (Ti,W)N/(Al,Sc)N metal/semiconductor superlattices. <i>Physical Review B</i> , 2016 , 93,	3.3	55
168	Thermal conductivity of bismuth telluride nanowire array-epoxy composite. <i>Applied Physics Letters</i> , 2009 , 94, 223116	3.4	54
167	Epitaxial CoGa and textured CoAs contacts on Ga _{1-x} Al _x As fabricated by molecular-beam epitaxy. <i>Journal of Applied Physics</i> , 1989 , 65, 4753-4758	2.5	54
166	Changing the academic culture: valuing patents and commercialization toward tenure and career advancement. <i>Proceedings of the National Academy of Sciences of the United States of America</i> , 2014 , 111, 6542-7	11.5	53

165	Dendrimer-assisted controlled growth of carbon nanotubes for enhanced thermal interface conductance. <i>Nanotechnology</i> , 2007 , 18, 385303	3-4	53
164	Microstructure of epitaxial La _{0.5} Sr _{0.5} CoO ₃ /ferroelectric Pb _{0.9} La _{0.1} (Zr _{0.2} Ti _{0.8}) _{0.975} O ₃ /La _{0.5} Sr _{0.5} CoO ₃ heterostructures on LaAlO ₃ . <i>Applied Physics Letters</i> , 1993 , 63, 1628-1630	3-4	53
163	Structural and optical quality of GaN/metal/Si heterostructures fabricated by excimer laser lift-off. <i>Applied Physics Letters</i> , 1999 , 75, 1887-1889	3-4	52
162	Epitaxial ferroelectric thin films for memory applications. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1994 , 22, 283-289	3-1	50
161	Stable and shallow PdIn ohmic contacts to n-GaAs. <i>Applied Physics Letters</i> , 1990 , 56, 2129-2131	3-4	50
160	Vertical single- and double-walled carbon nanotubes grown from modified porous anodic alumina templates. <i>Nanotechnology</i> , 2006 , 17, 3925-3929	3-4	49
159	Ni-InP reaction: Formation of amorphous and crystalline ternary phases. <i>Applied Physics Letters</i> , 1987 , 50, 1346-1348	3-4	49
158	Compound semiconductor contact metallurgy. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1988 , 1, 289-312	3-1	49
157	Near-surface defects formed during rapid thermal annealing of preamorphized and BF ₂ -implanted silicon. <i>Applied Physics Letters</i> , 1984 , 45, 982-984	3-4	49
156	High resolution transmission electron microscopy study of Se ⁺ -implanted and annealed GaAs: Mechanisms of amorphization and recrystallization. <i>Applied Physics Letters</i> , 1984 , 44, 623-625	3-4	49
155	Structural and chemical characterization of free-standing GaN films separated from sapphire substrates by laser lift-off. <i>Applied Physics Letters</i> , 2000 , 77, 1819	3-4	47
154	Phase formation in the Pd-InP system. <i>Journal of Applied Physics</i> , 1988 , 64, 4909-4913	2-5	47
153	Electro-optic properties of single crystalline ferroelectric thin films. <i>Applied Physics Letters</i> , 1993 , 63, 596-598	3-4	46
152	NiAl/n-GaAs Schottky diodes: Barrier height enhancement by high-temperature annealing. <i>Applied Physics Letters</i> , 1988 , 52, 1338-1340	3-4	46
151	Scaling of ferroelectric properties in La-Sr-Co-O/Pb-La-Zr-Ti-O/La-Sr-Co-O capacitors. <i>Applied Physics Letters</i> , 1994 , 64, 1588-1590	3-4	45
150	Epitaxial ferroelectric (Pb, La)(Zr, Ti)O ₃ thin films on stainless steel by excimer laser liftoff. <i>Applied Physics Letters</i> , 2000 , 76, 227-229	3-4	44
149	Galvanomagnetic properties of epitaxial MnAl films on GaAs. <i>Journal of Applied Physics</i> , 1991 , 69, 4689-4691	3-1	44
148	Integration of GaN thin films with dissimilar substrate materials by Pd-In metal bonding and laser lift-off. <i>Journal of Electronic Materials</i> , 1999 , 28, 1409-1413	1-9	43

147	Rocksalt nitride metal/semiconductor superlattices: A new class of artificially structured materials. <i>Applied Physics Reviews</i> , 2018 , 5, 021101	17.3	42
146	Compensation of native donor doping in ScN: Carrier concentration control and p-type ScN. <i>Applied Physics Letters</i> , 2017 , 110, 252104	3.4	42
145	Thermal conductivity of skutterudite thin films and superlattices. <i>Applied Physics Letters</i> , 2000 , 77, 3854-3856	3.4	42
144	TiN/(Al,Sc)N metal/dielectric superlattices and multilayers as hyperbolic metamaterials in the visible spectral range. <i>Physical Review B</i> , 2014 , 90,	3.3	41
143	An investigation of the Pd-In-Ge nonspiking Ohmic contact to n-GaAs using transmission line measurement, Kelvin, and Cox and Strack structures. <i>Journal of Applied Physics</i> , 1991 , 69, 4364-4372	2.5	41
142	Development of epitaxial Al _x Sc _{1-x} N for artificially structured metal/semiconductor superlattice metamaterials. <i>Physica Status Solidi (B): Basic Research</i> , 2015 , 252, 251-259	1.3	40
141	Electronic structure, vibrational spectrum, and thermal properties of yttrium nitride: A first-principles study. <i>Journal of Applied Physics</i> , 2011 , 109, 073720	2.5	40
140	Epitaxial MnGa/NiGa magnetic multilayers on GaAs. <i>Applied Physics Letters</i> , 1993 , 63, 696-698	3.4	40
139	Schottky barrier degradation of the W/GaAs system after high-temperature annealing. <i>Journal of Applied Physics</i> , 1986 , 60, 3235-3242	2.5	40
138	Dislocation-pipe diffusion in nitride superlattices observed in direct atomic resolution. <i>Scientific Reports</i> , 2017 , 7, 46092	4.9	39
137	High Resolution Observations of Copper Vacancy Ordering in Chalcocite (Cu ₂ S) and the Transformation to Djurleite (Cu _{1.97} to 1.94S). <i>Physica Status Solidi A</i> , 1982 , 72, 551-559		39
136	Electronic and optical properties of ScN and (Sc,Mn)N thin films deposited by reactive DC-magnetron sputtering. <i>Journal of Applied Physics</i> , 2013 , 114, 063519	2.5	38
135	Dendrimer-templated Fe nanoparticles for the growth of single-wall carbon nanotubes by plasma-enhanced CVD. <i>Journal of Physical Chemistry B</i> , 2006 , 110, 10636-44	3.4	38
134	Machining of transparent materials using an IR and UV nanosecond pulsed laser. <i>Applied Physics A: Materials Science and Processing</i> , 2000 , 71, 601-608	2.6	38
133	Pulsed laser deposition of skutterudite thin films. <i>Journal of Applied Physics</i> , 2001 , 89, 3508-3513	2.5	36
132	MBE growth of ferromagnetic metastable epitaxial MnAl thin films on AlAs/GaAs heterostructures. <i>Journal of Crystal Growth</i> , 1991 , 111, 978-983	1.6	36
131	Energy deposition at front and rear surfaces during picosecond laser interaction with fused silica. <i>Applied Physics Letters</i> , 2001 , 78, 2840-2842	3.4	32
130	Phonon wave effects in the thermal transport of epitaxial TiN/(Al,Sc)N metal/semiconductor superlattices. <i>Journal of Applied Physics</i> , 2017 , 121, 015109	2.5	31

129	Template approaches to growth of oriented oxide heterostructures on SiO ₂ /Si. <i>Journal of Electronic Materials</i> , 1994 , 23, 19-23	1.9	31
128	Highly ordered diamond and hybrid triangle-diamond patterns in porous anodic alumina thin films. <i>Applied Physics Letters</i> , 2008 , 93, 043108	3.4	30
127	Reaction of amorphous Ni-W and Ni-N-W films with substrate silicon. <i>Journal of Applied Physics</i> , 1984 , 56, 2740-2745	2.5	30
126	Room temperature device performance of electrodeposited InSb nanowire field effect transistors. <i>Applied Physics Letters</i> , 2011 , 98, 243504	3.4	29
125	High resolution structural characterization of the amorphous-crystalline interface in Se ⁺ -implanted GaAs. <i>Applied Physics Letters</i> , 1984 , 44, 874-876	3.4	29
124	Effect of deposition pressure on the microstructure and thermoelectric properties of epitaxial ScN(001) thin films sputtered onto MgO(001) substrates. <i>Journal of Materials Research</i> , 2015 , 30, 626-634	2.5	28
123	Lithography-free in situ Pd contacts to templated single-walled carbon nanotubes. <i>Nano Letters</i> , 2006 , 6, 2712-7	11.5	27
122	Optical spectroscopy of GaN microcavities with thicknesses controlled using a plasma etchback. <i>Applied Physics Letters</i> , 2001 , 79, 3029-3031	3.4	27
121	Temperature-dependent thermal and thermoelectric properties of n-type and p-type Sc _{1-x} Mg _x N. <i>Physical Review B</i> , 2018 , 97,	3.3	26
120	In/GaAs reaction: Effect of an intervening oxide layer. <i>Applied Physics Letters</i> , 1986 , 49, 818-820	3.4	26
119	Ternary phases in the Pd-GaAs system: Implications for shallow contacts to GaAs. <i>Materials Letters</i> , 1985 , 3, 409-413	3.3	26
118	Dendrimer-assisted low-temperature growth of carbon nanotubes by plasma-enhanced chemical vapor deposition. <i>Chemical Communications</i> , 2006 , 2899-901	5.8	25
117	Magneto-transport in ultrathin ErAs epitaxial layers buried in GaAs. <i>Surface Science</i> , 1990 , 228, 13-15	1.8	25
116	Electrical properties of individual gold nanowires arrayed in a porous anodic alumina template. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2007 , 204, 3152-3158	1.6	24
115	Effects of KrF excimer laser irradiation on metal contacts to n-type and p-type GaN. <i>Journal of Applied Physics</i> , 2003 , 94, 3529-3535	2.5	24
114	Magnetic manipulation and optical imaging of an active plasmonic single-particle Fe-Au nanorod. <i>Langmuir</i> , 2011 , 27, 15292-8	4	23
113	High resolution transmission electron microscopy of proton-implanted gallium arsenide. <i>Applied Physics Letters</i> , 1985 , 47, 691-693	3.4	23
112	Thermal stability of epitaxial cubic-TiN/(Al,Sc)N metal/semiconductor superlattices. <i>Journal of Materials Science</i> , 2015 , 50, 3200-3206	4.3	22

111	III-nitride nanopyramid light emitting diodes grown by organometallic vapor phase epitaxy. <i>Journal of Applied Physics</i> , 2010 , 108, 044303	2.5	22
110	Growth of TiN/GaN metal/semiconductor multilayers by reactive pulsed laser deposition. <i>Journal of Applied Physics</i> , 2006 , 100, 064901	2.5	22
109	Enhancement of (In,Ga)N light-emitting diode performance by laser liftoff and transfer from sapphire to silicon. <i>IEEE Photonics Technology Letters</i> , 2002 , 14, 1400-1402	2.2	22
108	Simple Ru electrode scheme for ferroelectric (Pb,La)(Zr,Ti)O ₃ capacitors directly on silicon. <i>Journal of Applied Physics</i> , 1998 , 84, 1121-1125	2.5	22
107	Decoupling the structural and magnetic phase transformations in magneto-optic MnBi thin films by the partial substitution of Cr for Mn. <i>Applied Physics Letters</i> , 1998 , 72, 2337-2339	3.4	22
106	Enhanced hardness in epitaxial TiAlScN alloy thin films and rocksalt TiN/(Al,Sc)N superlattices. <i>Applied Physics Letters</i> , 2014 , 105, 151904	3.4	21
105	Epitaxial metal(NiAl)-semiconductor(IIIIV) heterostructures by MBE. <i>Surface Science</i> , 1990 , 228, 1-8	1.8	21
104	Toward surround gates on vertical single-walled carbon nanotube devices. <i>Journal of Vacuum Science & Technology B</i> , 2009 , 27, 821		20
103	Controlled Decoration of Single-Walled Carbon Nanotubes with Pd Nanocubes. <i>Journal of Physical Chemistry C</i> , 2007 , 111, 13756-13762	3.8	20
102	In-place fabrication of nanowire electrode arrays for vertical nanoelectronics on Si substrates. <i>Journal of Vacuum Science & Technology B</i> , 2007 , 25, 343		20
101	Optical properties of metallic quantum wells. <i>IEEE Journal of Quantum Electronics</i> , 1992 , 28, 1663-1669	2	20
100	First-principles analysis of ZrN/ScN metal/semiconductor superlattices for thermoelectric energy conversion. <i>Journal of Applied Physics</i> , 2011 , 109, 083717	2.5	19
99	Electrical properties of metal contacts on laser-irradiated n-type GaN. <i>Applied Physics Letters</i> , 2003 , 82, 580-582	3.4	19
98	Microstructural evolution and thermal stability of HfN/ScN, ZrN/ScN, and Hf _{0.5} Zr _{0.5} N/ScN metal/semiconductor superlattices. <i>Journal of Materials Science</i> , 2016 , 51, 8250-8258	4.3	18
97	Thermoelectric properties of HfN/ScN metal/semiconductor superlattices: a first-principles study. <i>Journal of Physics Condensed Matter</i> , 2012 , 24, 415303	1.8	18
96	Kinetics of the Pd/In thin-film bilayer reaction: Implications for transient-liquid-phase wafer bonding. <i>Journal of Electronic Materials</i> , 2001 , 30, 1471-1475	1.9	18
95	Epitaxial growth of semiconducting LaVO ₃ thin films. <i>Journal of Materials Research</i> , 2000 , 15, 1-3	2.5	18
94	Crystallographic relationships between GaAs, As and Ga ₂ O ₃ at the GaAs-thermal oxide interface. <i>Materials Letters</i> , 1985 , 3, 247-250	3.3	18

93	Capacitance-voltage modeling of metal-ferroelectric-semiconductor capacitors based on epitaxial oxide heterostructures. <i>Applied Physics Letters</i> , 2011 , 98, 102901	3.4	17
92	Organometallic vapor phase epitaxial growth of GaN on ZrN/AlN/Si substrates. <i>Applied Physics Letters</i> , 2008 , 93, 023109	3.4	17
91	Independently addressable fields of porous anodic alumina embedded in SiO ₂ on Si. <i>Applied Physics Letters</i> , 2008 , 92, 013122	3.4	17
90	Microfabrication using one-step LPCVD porous polysilicon films. <i>Journal of Microelectromechanical Systems</i> , 2003 , 12, 418-424	2.5	17
89	Modification of (Pb,La)(Zr,Ti)O ₃ thin films during pulsed laser liftoff from MgO substrates. <i>Journal of Applied Physics</i> , 2003 , 94, 4047-4052	2.5	17
88	Backside secondary ion mass spectrometry study of a Ge/Pd ohmic contact to InP. <i>Applied Physics Letters</i> , 1992 , 60, 1123-1125	3.4	17
87	Electrical resistivity of thin epitaxial NiAl buried in (Al,Ga)As. <i>Applied Physics Letters</i> , 1989 , 54, 2112-2114	3.4	17
86	Chemical effects in ion mixing of a ternary system (metal-SiO ₂). <i>Applied Physics Letters</i> , 1987 , 50, 571-573	3.4	17
85	Fluence effects on the magnetic properties of Fe ₈₁ B _{13.5} Si _{3.5} C ₂ metallic glass produced by pulsed laser deposition. <i>Journal of Applied Physics</i> , 1999 , 85, 6652-6654	2.5	16
84	Non-volatile memory characteristics of submicrometre Hall structures fabricated in epitaxial ferromagnetic MnAl films on GaAs. <i>Electronics Letters</i> , 1993 , 29, 421	1.1	16
83	Correlation between solid-state reaction and electrical properties of the Rh/GaAs Schottky contact. <i>Journal of Applied Physics</i> , 1987 , 61, 1099-1102	2.5	16
82	Self-supporting nanowire arrays templated in sacrificial branched porous anodic alumina for thermoelectric devices. <i>Applied Physics Letters</i> , 2009 , 95, 073108	3.4	15
81	The Si/Pd(Si,Ge) ohmic contact on n-GaAs. <i>Applied Physics Letters</i> , 1992 , 60, 3016-3018	3.4	15
80	Thin film YBaCuO high superconductors: structure-property relationships. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1992 , 14, 188-213	3.1	15
79	Selective-area epitaxy of GaAs through silicon dioxide windows by molecular beam epitaxy. <i>Applied Physics Letters</i> , 1986 , 48, 142-144	3.4	15
78	Tailoring of surface plasmon resonances in TiN/(Al _{0.72} Sc _{0.28})N multilayers by dielectric layer thickness variation. <i>Journal of Materials Science</i> , 2018 , 53, 4001-4009	4.3	15
77	Optimization of carbon nanotube synthesis from porous anodic AlFeAl templates. <i>Carbon</i> , 2007 , 45, 2290-2296	10.4	14
76	High-T _c superconducting NbN films with low particulate density grown at 25 °C using pulsed laser deposition. <i>Journal of Materials Research</i> , 2001 , 16, 1223-1226	2.5	14

75	Cross-plane thermoelectric transport in p-type La _{0.67} Sr _{0.33} MnO ₃ /LaMnO ₃ oxide metal/semiconductor superlattices. <i>Journal of Applied Physics</i> , 2013 , 113, 193702	2.5	13
74	Thermomechanical and Thermal Contact Characteristics of Bismuth Telluride Films Electrodeposited on Carbon Nanotube Arrays. <i>Advanced Materials</i> , 2009 , 21, 4280-4283	24	13
73	Magnetic and magneto-optic properties of epitaxial ferromagnetic MnAl/(Al,Ga)As heterostructures. <i>Applied Physics Letters</i> , 1992 , 60, 1393-1395	3.4	13
72	Interfacial interactions of evaporated iridium thin films with (100) GaAs. <i>Journal of Applied Physics</i> , 1987 , 62, 1815-1820	2.5	13
71	Templated synthesis of gold-iron alloy nanoparticles using pulsed laser deposition. <i>Nanotechnology</i> , 2006 , 17, 5131-5135	3.4	12
70	Bimodal spatial distribution of pores in anodically oxidized aluminum thin films. <i>Journal of Applied Physics</i> , 2000 , 88, 6875-6880	2.5	12
69	Epitaxial MnAl/NiAl magnetic multilayers on AlAs/GaAs. <i>Applied Physics Letters</i> , 1993 , 63, 839-841	3.4	12
68	Electrodeposition of InSb branched nanowires: Controlled growth with structurally tailored properties. <i>Journal of Applied Physics</i> , 2014 , 116, 083506	2.5	11
67	Pseudomorphic stabilization of rocksalt GaN in TiN/GaN multilayers and superlattices. <i>Physical Review B</i> , 2009 , 80,	3.3	11
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